

AMENDMENTS TO THE CLAIMS

B
Claim 1 (Currently Amended): A ceramic heater for a semiconductor-producing/examining device having, the ceramic heater comprising
a ceramic substrate having a disc form including two opposing surfaces; and
a resistance heating element formed on a surface one of the two opposing surfaces of a
the ceramic substrate or inside a the ceramic substrate, wherein said
the ceramic substrate is made of comprises a non-oxide ceramic containing 0.05 to 5%
by weight of oxygen; and
the non-oxide ceramic has a maximum pore diameter of ~~the maximum pore thereof~~ is
50 5 μm or less.

Claim 2 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said non-oxide ceramic is a nitride
ceramic.

Claim 3 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said non-oxide ceramic is a
carbide ceramic.

Claim 4 (Canceled)

Claim 5 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate has a
porosity of 5% or less.

Claim 6 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate is capable
of use within the temperature range of 100 to 700°C.

B
Claim 7 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate has a
thickness of 25 mm or less, and a diameter of 200 mm or more.

Claim 8 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate has a
plurality of through holes into which lifter pins for a semiconductor wafer are capable of
being inserted.

Claim 9 (Canceled)

Claim 10 (Currently Amended): The ceramic heater ~~for the semiconductor-~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate contains
oxygen in an amount of 0.1 to 5% by weight.

Claim 11 (Currently Amended): The ceramic heater ~~for the semiconductor=~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate comprises
an alkali metal oxide, an alkali earth metal oxide, or a rare earth element oxide.

Claim 12 (Currently Amended): The ceramic heater ~~for the semiconductor=~~
~~producing/examining device~~ according to claim 1, wherein an electrostatic electrode or an RF
electrode is embedded inside the ceramic substrate.

b Claim 13 (Currently Amended): The ceramic heater ~~for the semiconductor=~~
~~producing/examining device~~ according to claim 1, wherein said heating element is a Peltier
device.

Claim 14 (Currently Amended): The ceramic heater ~~for the semiconductor=~~
~~producing/examining device~~ according to claim 1, wherein said heating element is selected
from the group consisting of a conductive ceramic, a metal foil, a metal sintered body, and a
metal wire.

Claim 15 (Currently Amended): The ceramic heater ~~for the semiconductor=~~
~~producing/examining device~~ according to claim 1, wherein a chuck top conductor layer is
formed on the surface of said ceramic substrate.

Claim 16 (Currently Amended): The ceramic heater ~~for the semiconductor=~~
~~producing/examining device~~ according to claim 1, wherein said ceramic substrate contains
BN.

Claim 17 (New): A method of making a ceramic heater, the method comprising

sintering a raw material powder to form a ceramic substrate;

forming a resistance heating element on the ceramic substrate or inside the ceramic

substrate; and

producing the ceramic heater of Claim 1.
